



Machine Learning in Computational Lithography

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ASML-Brion

San Jose, February 2019

This is really a no-brainer ...



G Dan Hutcheson

What's Happening and *What's the Meaning:*

ASML introduces AI to its product portfolio: *This is really a no-brainer. That said, the problem that most equipment companies have is finding good applications for it, as they find all they have is little data to feed the NN (more on that below). Anyway, this will be a good test for DLNNs as to whether engineers will accept results without knowing what's in the 'blackbox,' which is a classic barrier to this technology. I believe they will because comparing results to input consistency are pretty easy to test out in this case. Especially since ASML led the way into computational lithography, albeit with plenty of customer pull.*

Source: **The Chip Insider**[®] VLSIresearch

Machine learning brings revolution to many applications!



Can machine learning be the moonshot for us?

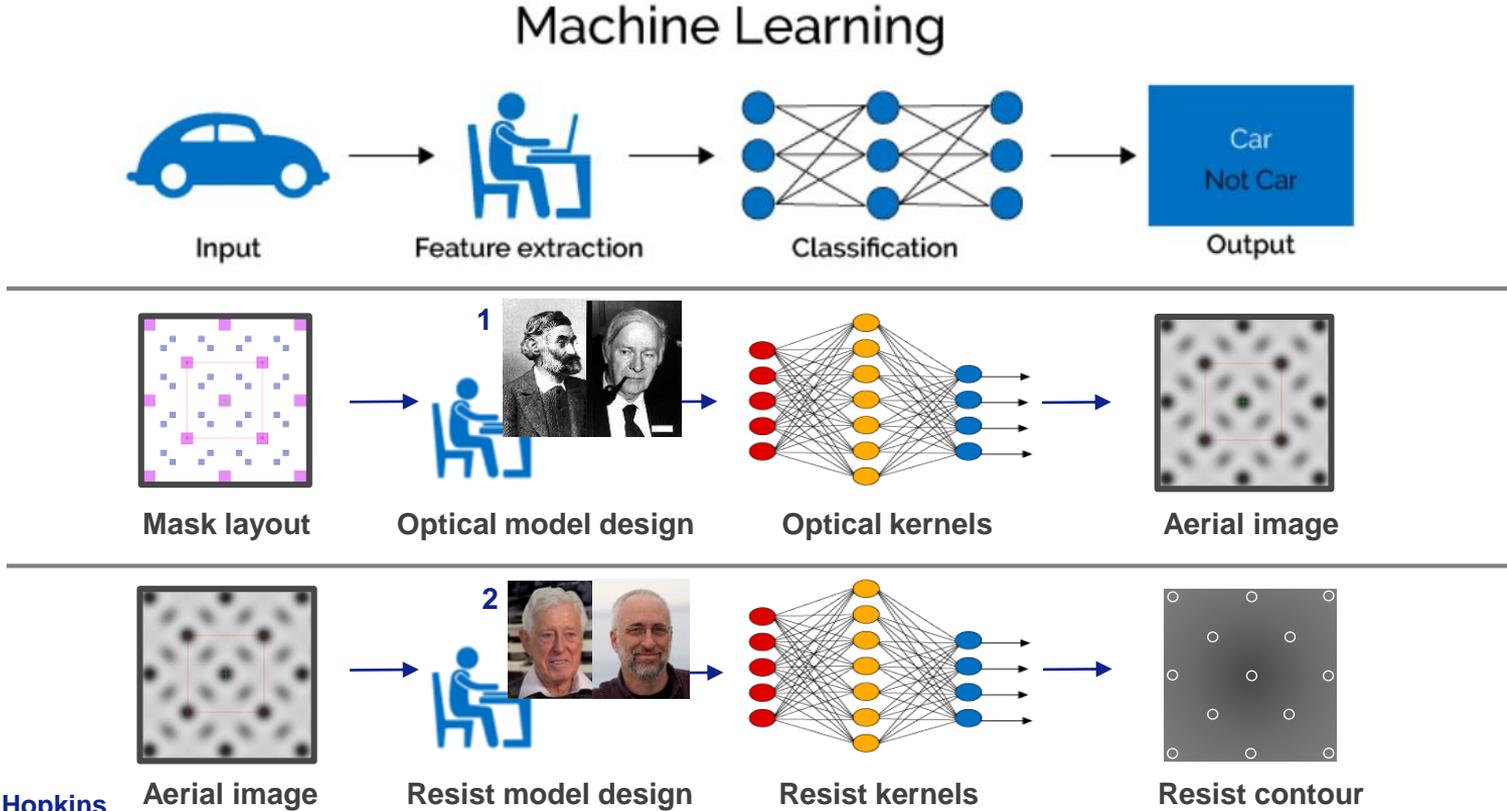


Rail: Driver Fatigue

Mining: Production Safety

Intruder Alerts

We have been doing machine learning for a long time ... *with manual feature engineering*



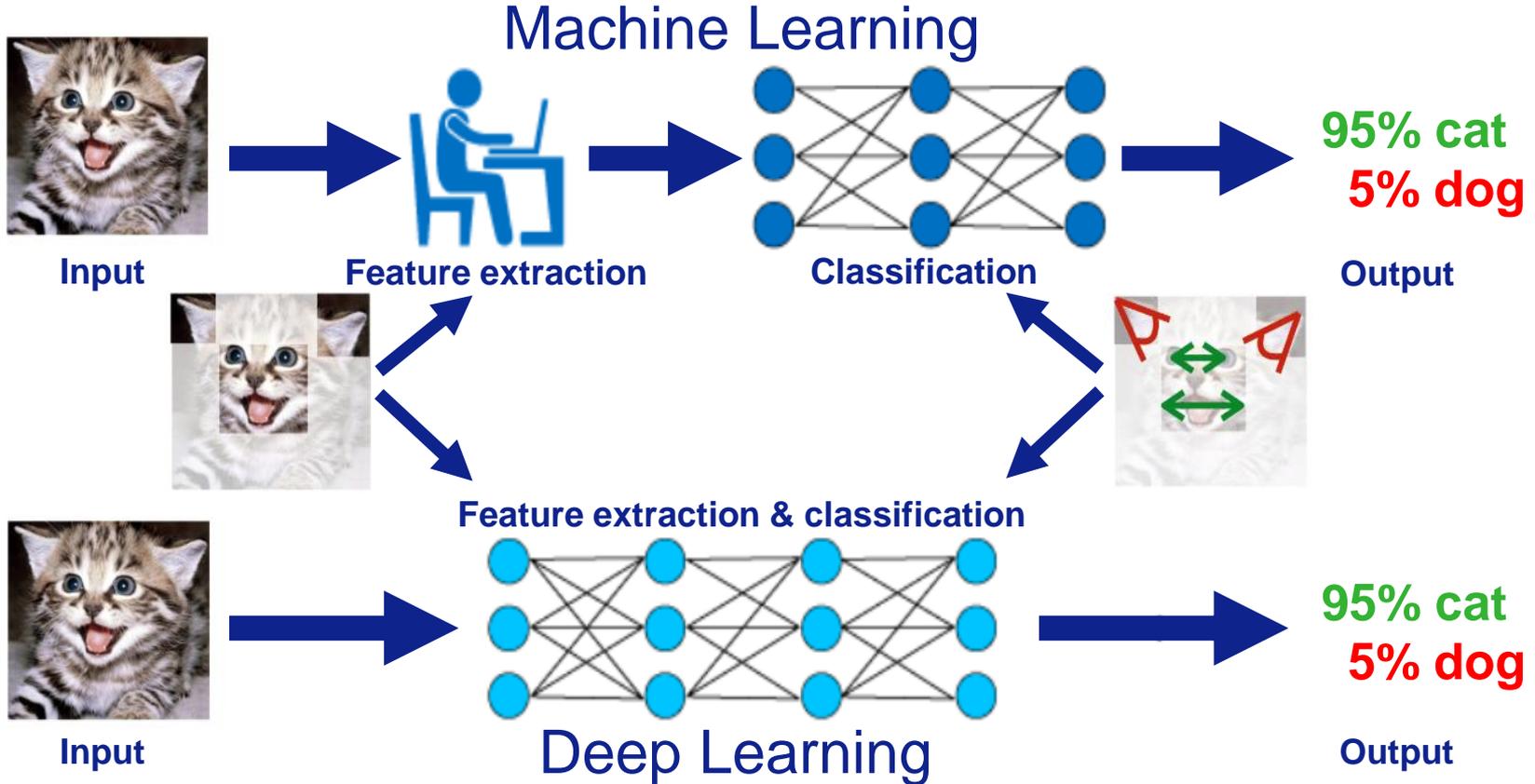
1: E. Abbe, H. H. Hopkins

2: F. H. Dill, C. Mack

Few hidden layers = Shallow neural network

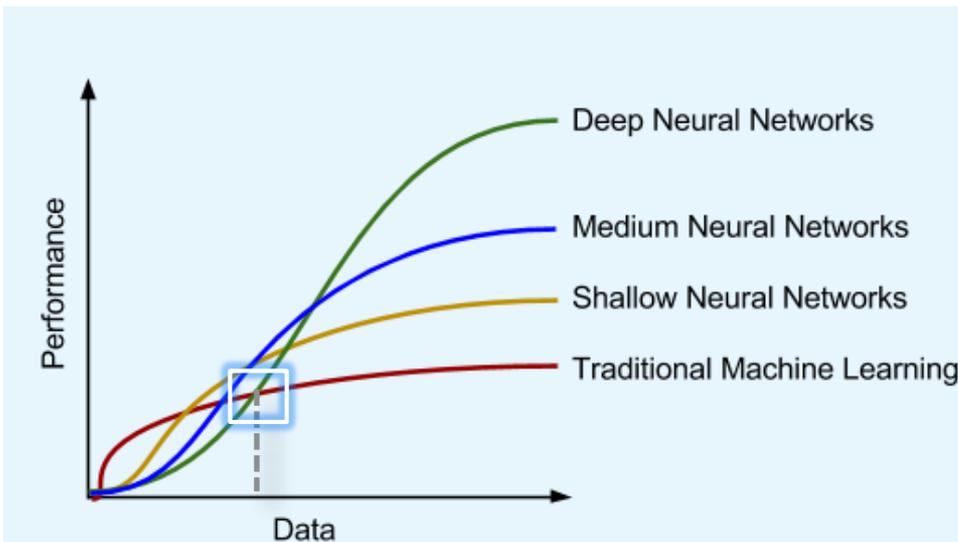
Machine Learning evolved to Deep Learning

Less human intervention in growing data volume analysis

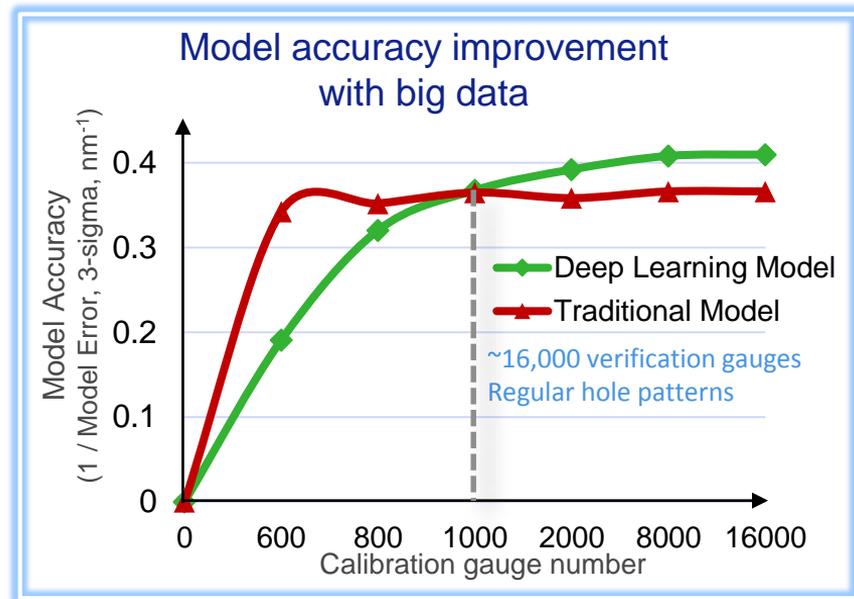


Massive metrology data & deep learning models further improve OPC accuracy in customer case

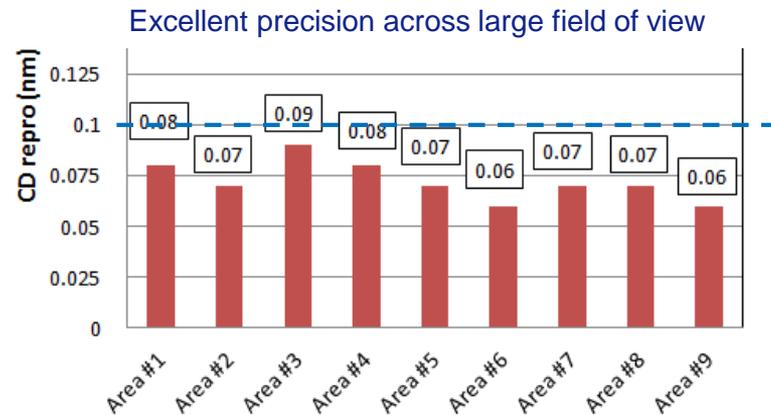
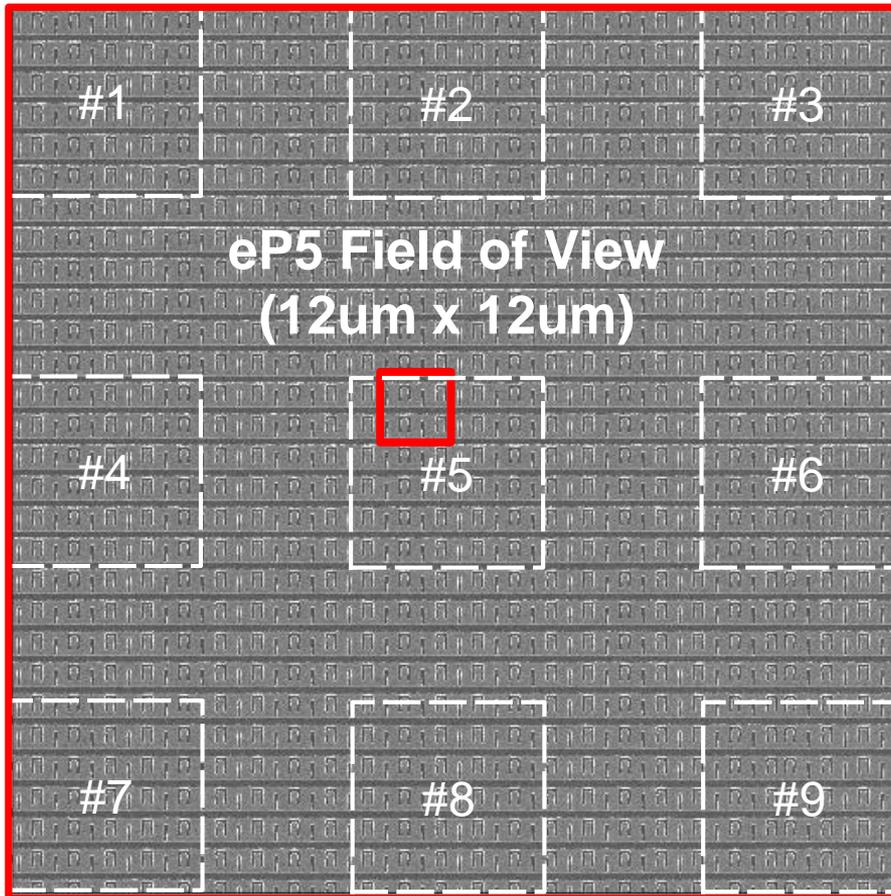
- Big data improve pattern coverage & enhance model accuracy
- Deep Learning Model has more benefits with big data vs Traditional Model



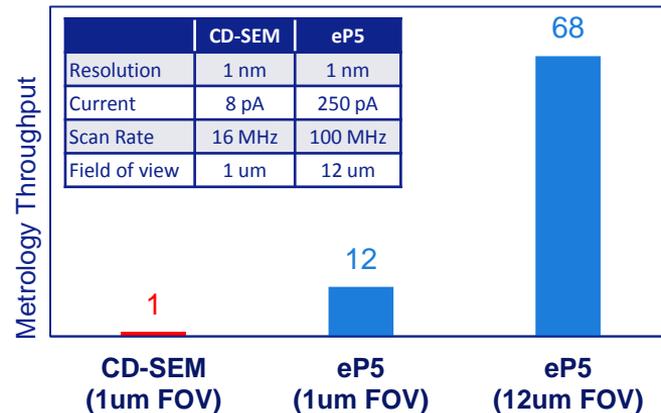
Source: Jeff Dean, Google, "Trends and developments in deep learning", Jan'17



High speed e-beam metrology and large field of view



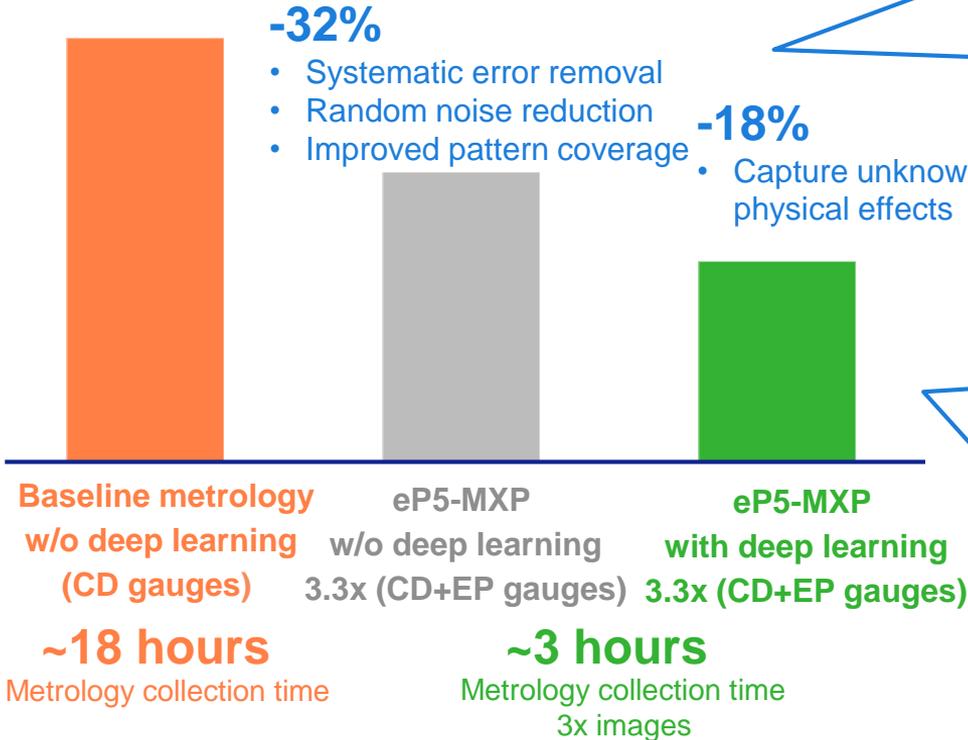
Throughput advantage over CD-SEM



Improving OPC model accuracy by 2X on DRAM

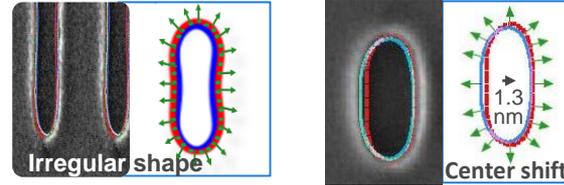
enabled by deep learning, fast e-beam, and metrology processing

Model prediction error (RMS)
validated with >150k Edge Placement (EP) Gauges



eP5-MXP metrology

Improving 2D metrology accuracy with contour based measurement

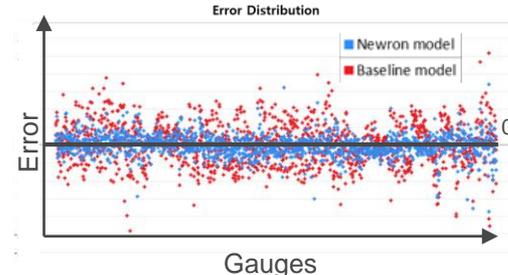


Systematic error reduction without shape fitting

EP gauges capture pattern shift

Deep learning resist model

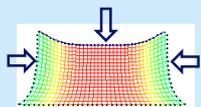
Improve OPC model accuracy



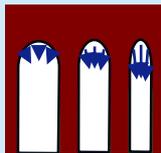
Better accuracy of lithography models by deep learning

Enabled by fast e-beam metrology and physical based models

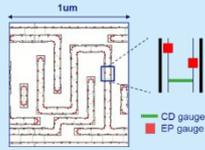
Physical driven **training** using physics based lithography models



Physical Resist Shrinkage

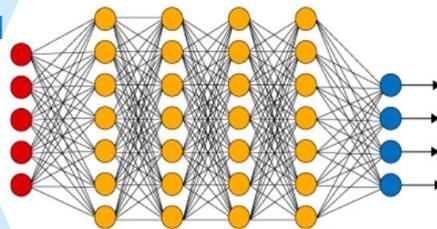


Resist surface stress

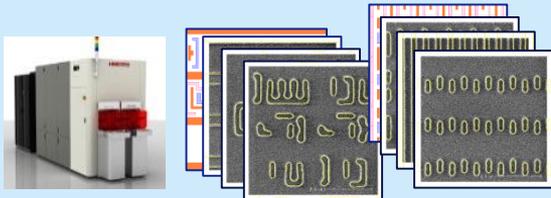


Data expansion through simulated contours

ASML Deep Learning model



Data-driven **training** based on fitting spec and wafer measurements



Large volume wafer metrology data, further enhanced by fast e-beam

Model Prediction Accuracy (RMS in nm)

EUV Cases: 7 nm and 5 nm logic



DUV Cases: 7 nm and 5 nm logic



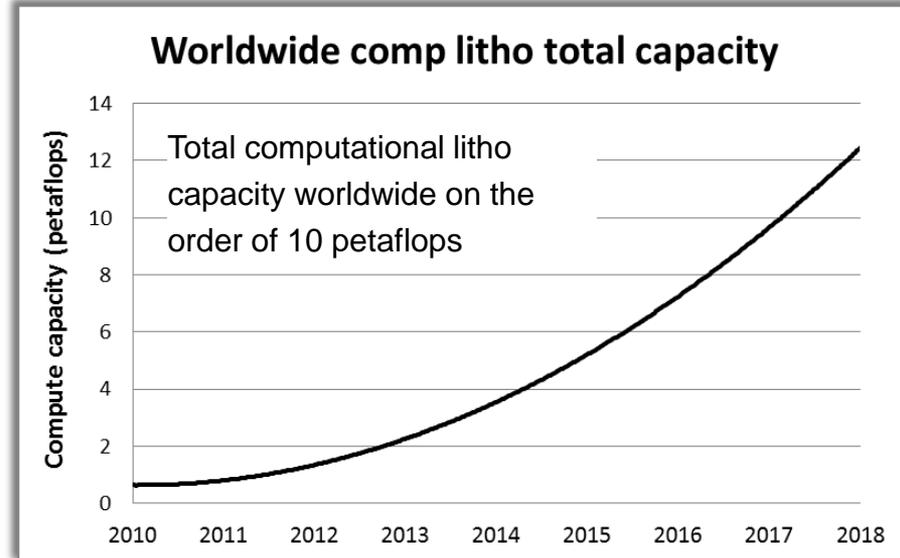
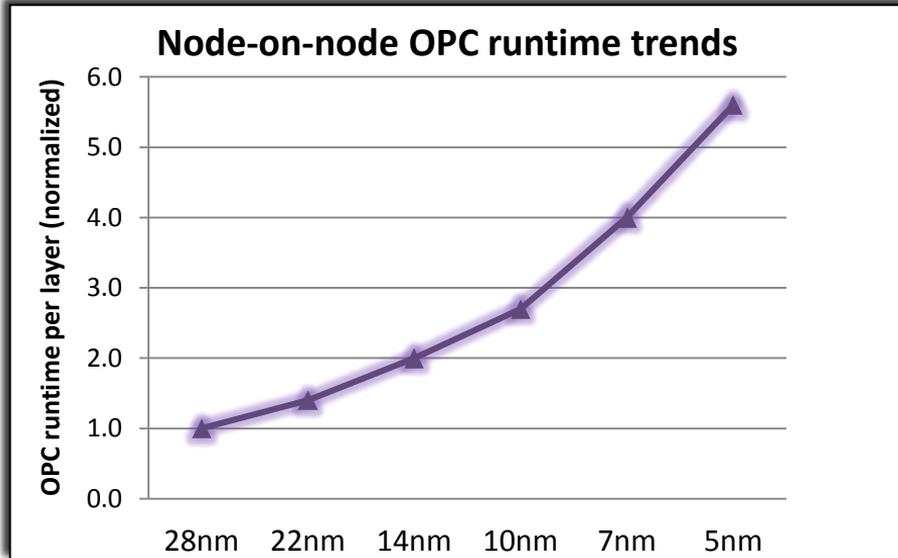
with Deep Learning
without Deep Learning

"EP SET1" → Edge Placement Gauge Set 1

“Moore’s Law” of Computational Lithography

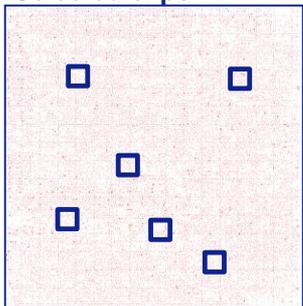
Runtime and cost of OPC increases node-by-node

| Technology Node | 28nm | 22nm | 14nm | 10nm | 7nm | 5nm |
|---|------|------|------|------|------|-------|
| Production start | 2011 | 2013 | 2014 | 2016 | 2017 | 2019 |
| Average transistor density (billion/cm ²) | 1.17 | 1.63 | 2.34 | 3.75 | 6.25 | 10.71 |
| Number of critical layer masks | 18 | 24 | 33 | 37 | 47 | 66 |
| Normalized OPC runtime per layer per unit area | 1 | 1.4 | 2 | 2.7 | 4 | 5.6 |



Deep learning inverse model speeds up full-chip OPC by providing a good starting point

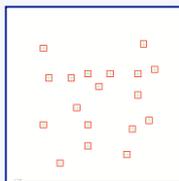
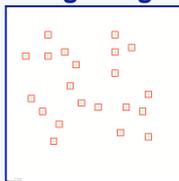
Selected clips



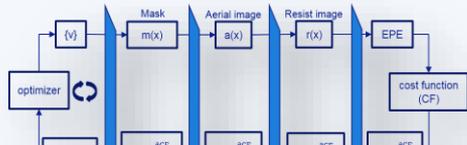
Training on clips



Design target

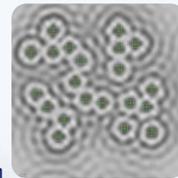


Training input

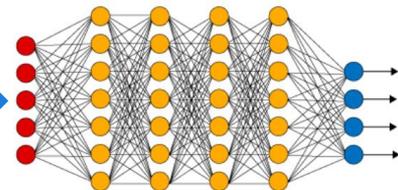


Complex, Iterative
Optimization

Inverse mask image



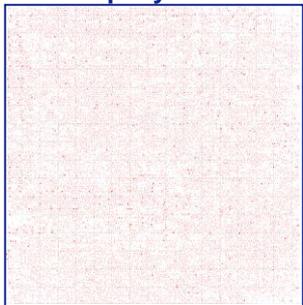
Training input



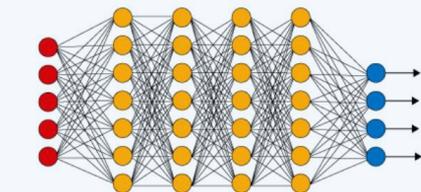
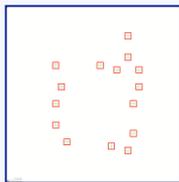
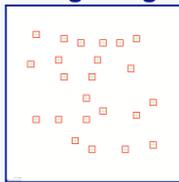
Deep Learning Inverse Model

Inference on full chip

Full chip layout

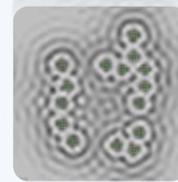
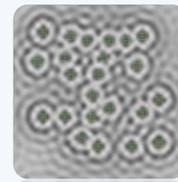


Design target



Deep Learning Inverse Model

Inverse mask image



Full chip layout (Post-OPC)



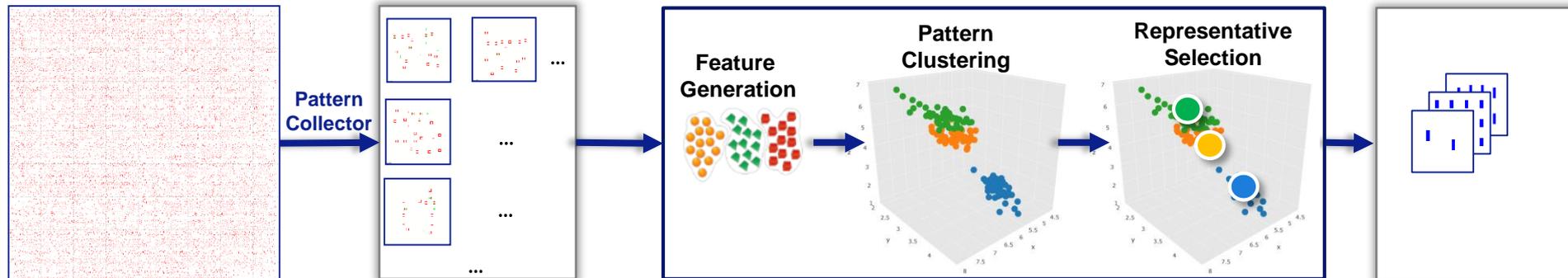
Improving training pattern coverage using machine-learning-based pattern selection

Full-chip Layout

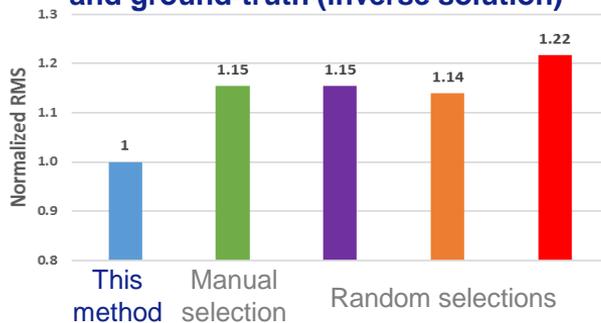
Pattern Library

Machine-learning-based pattern selection

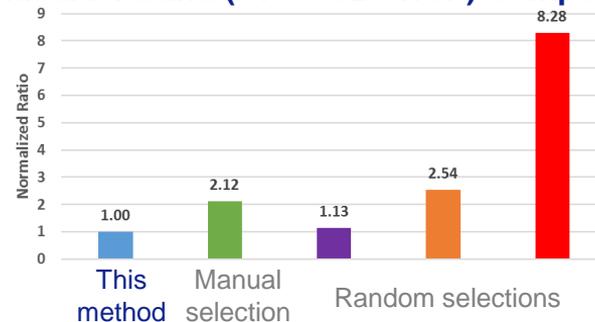
Training Pattern Set



Normalized RMS between prediction and ground-truth (inverse solution)



Critical PV-band (>15% CD error) Comparison



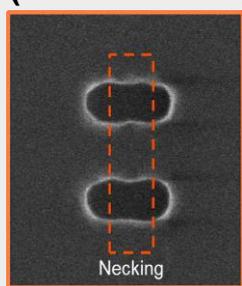
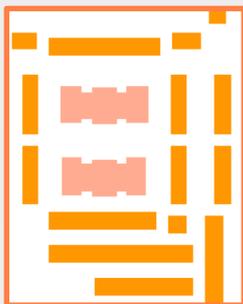
Deep learning SRAF improves full-chip DoF by 24% for DRAM contact hole layer, validated on wafer

Newron SRAF places more accurate assist features to remove the process window limiter

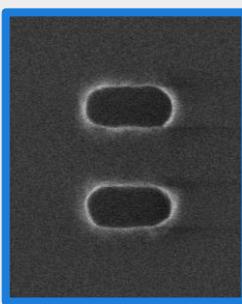
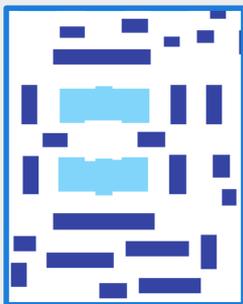
OPC Mask

Off-nominal (-40nm defocus)

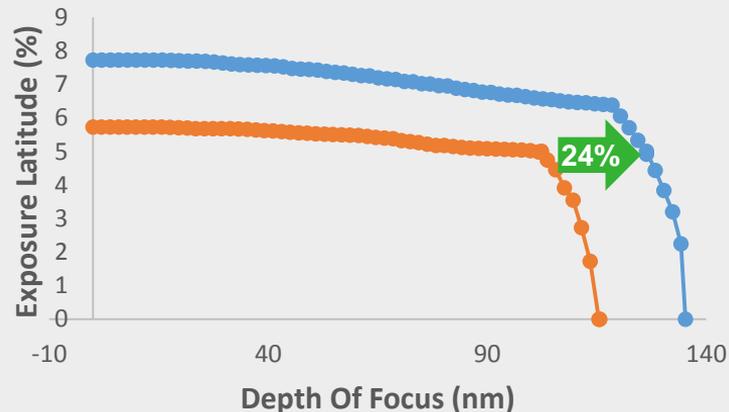
Baseline solution (Rule-Based SRAF)



Newron SRAF (Deep Learning)



Newron SRAF wafer validation shows 24% DoF improvement



| | Baseline (RB-SRAF) | Newron SRAF |
|-------------|--------------------|-------------|
| DOF @ 5% EL | 102 nm | 126 nm |

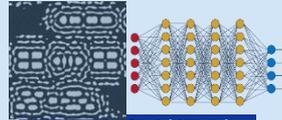
Leverage confluence of new technologies to meet OPC technology and cost requirements



ASML



Inverse OPC (CTM)



Inverse OPC (CTM+) Deep Learning Inverse



Inverse with phase control Hardware Accel. (tentative)

intel



Intel Xeon Processor E5 v4



Skylake

Intel DL Boost



Cascade Lake



Cooper Lake

14 → 10 nm



Ice Lake



Intel Xeon Scalable processor with integrated FPGA



Nervana Spring Crest

nvidia



Pascal



Volta

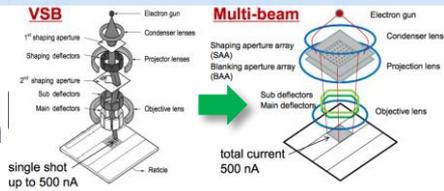


Turing



Next Gen?

Mask writer & inspection

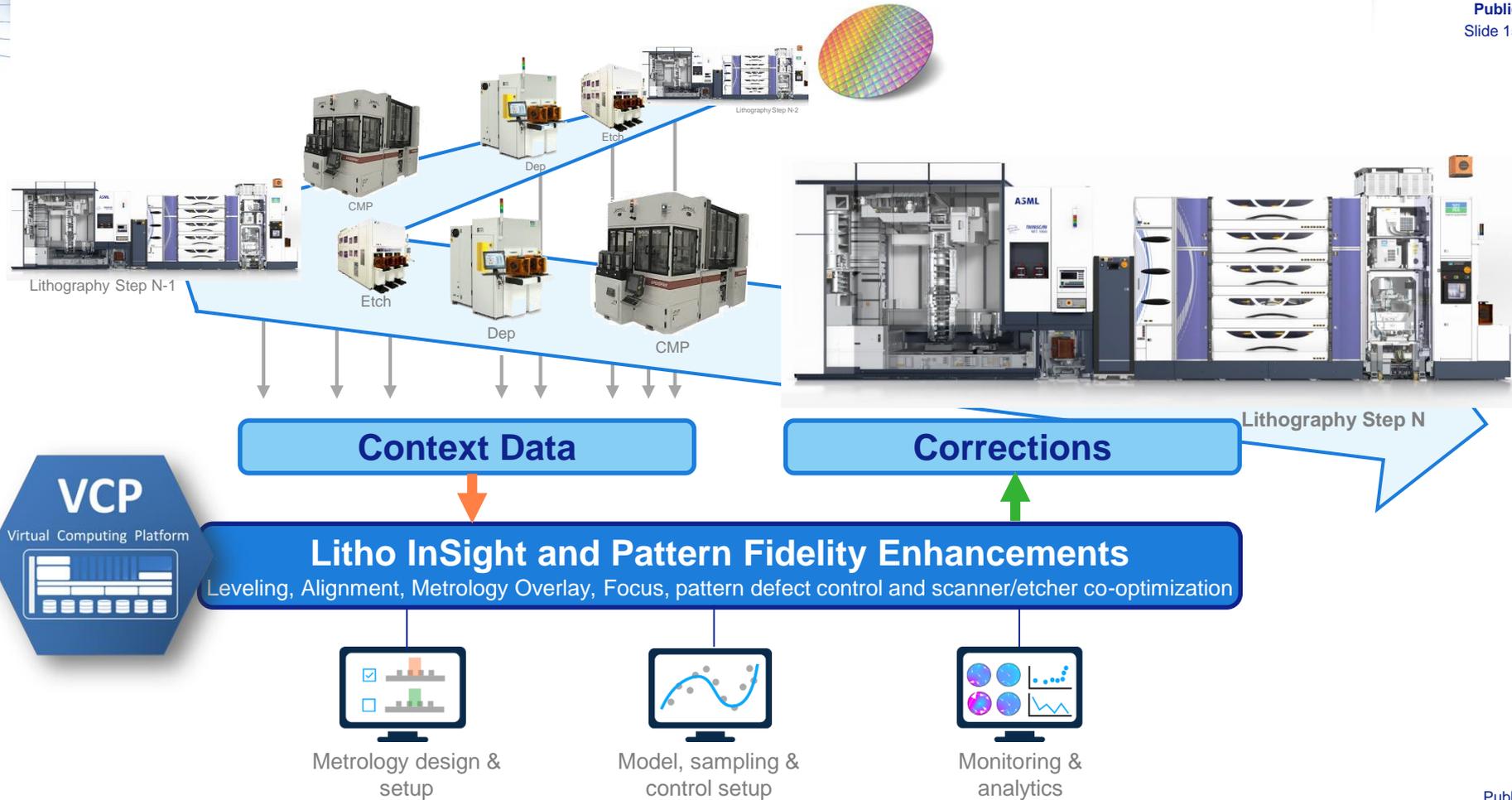


Mask inspection available

Multi-beam Mask Writer available

Mask making infrastructure is ready for inverse OPC & curvi-linear masks

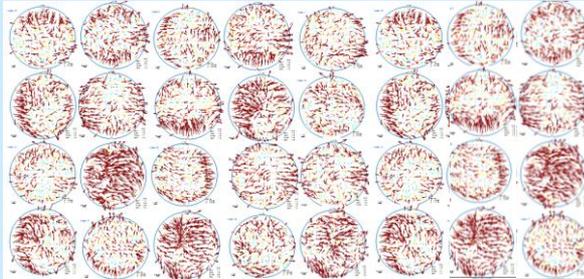
Context-aware control extends holistic solutions



Leverage machine learning to address wafer-to-wafer variation induced by different wafer process routes

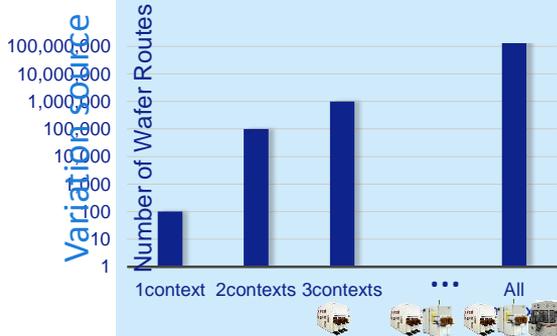
Wafer to Wafer Variation

Overlay Variations

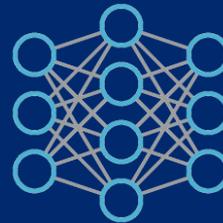


Every month > 100,000 wafers exposed per scanner

Different Process Route

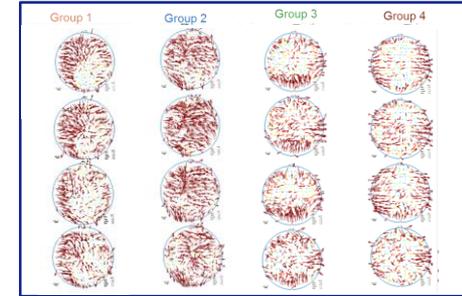


ASML Machine Learning Model

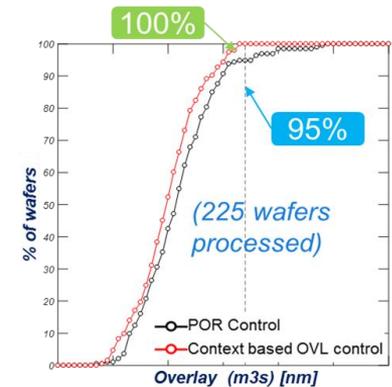


Correlate wafer-to-wafer variation to process context and apply run-to-run control with context-based grouping

Context based Overlay Control results



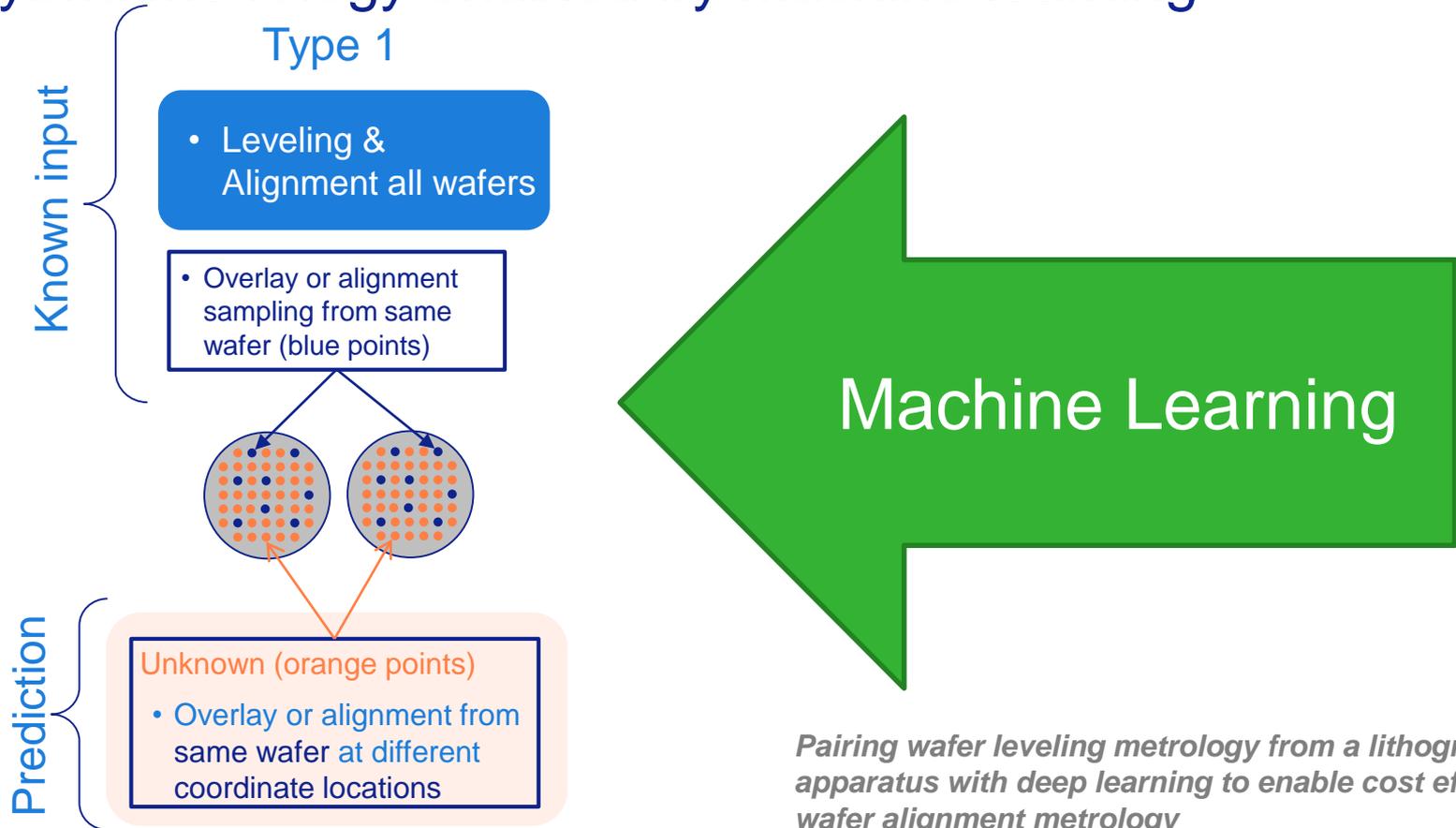
Wafers in spec



A novel patterning control strategy based on real-time fingerprint recognition and adaptive wafer level scanner optimization

H. E. Hakli et al., SPIE 2018, 10585:105851N

Predict dense alignment from dense leveling data hybrid metrology enabled by machine learning



Pairing wafer leveling metrology from a lithographic apparatus with deep learning to enable cost effective dense wafer alignment metrology

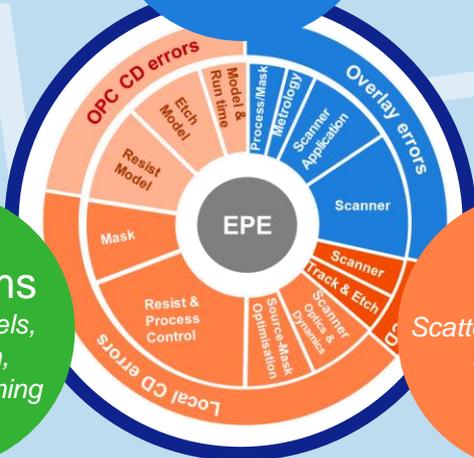
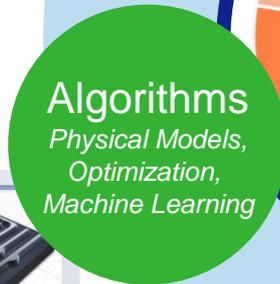
E. Schmitt-Weaver & K. Bhattacharyya, SPIE 2019, 10961-7

Holistic Lithography delivering significant customer value

Lithography scanner with advanced control capability



Etch and deposition tools

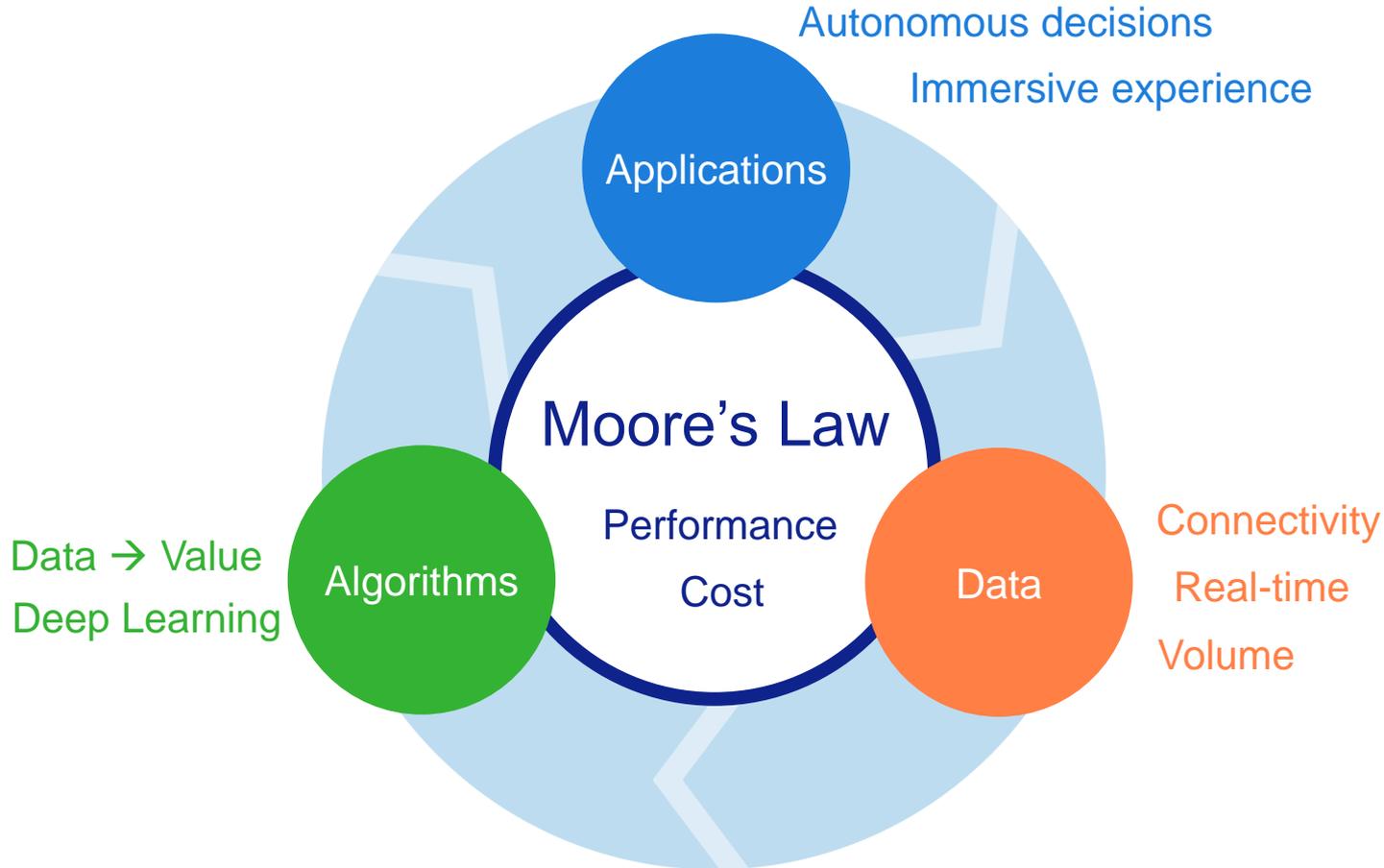


Computational lithography and metrology



Optical and e-beam metrology

Major trends in semiconductor-enabled computing



The image features the ASML logo in a bold, dark blue font on the left side. The background is a light blue gradient with several decorative elements: a large, semi-transparent light blue arc in the upper left; a series of thin, white, wavy lines that originate from the right side of the ASML text and extend across the lower half of the image; and a solid light blue area in the upper right.

ASML